


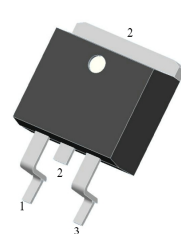

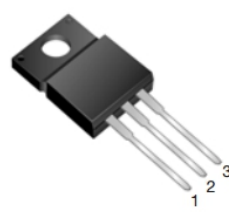
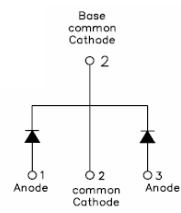
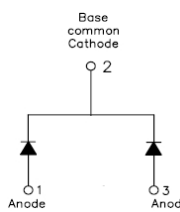
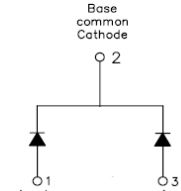
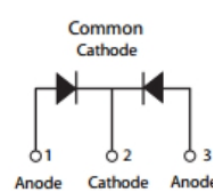
## ST10100C/STB10100C/STF10100C/STD10100C SCHOTTKY RECTIFIER

### Applications

- Switching power supply
- Converters
- Free-Wheeling diodes
- Reverse battery protection

### Features

- 150 °C T<sub>J</sub> operation
- Ultralow forward voltage drop
- High purity, high temperature epoxy encapsulation for enhanced mechanical strength and moisture resistance
- High frequency operation
- Guard ring for enhanced ruggedness and long term reliability
- Trench MOS Schottky technology
- Terminals finish: 100% Pure Tin
- This is a Pb – Free Device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request

ST10100C	STB10100C	STD10100C	STF10100C
			
			
TO-220AB	D <sup>2</sup> PAK	DPAK	ITO-220AB

### Maximum Ratings:

Characteristics	Symbol	Condition	Max.	Units
Peak Repetitive Reverse Voltage	V <sub>RRM</sub>	-	100	V
Working Peak Reverse Voltage	V <sub>RWM</sub>			
DC Blocking Voltage	V <sub>R</sub>			
Average Rectified Forward Current	I <sub>F(AV)</sub>	50% duty cycle @T <sub>c</sub> =100°C, rectangular wave form	5(Per Leg) 10(Per Device)	A
Peak One Cycle Non-Repetitive Surge Current(Per Leg)	I <sub>FSM</sub>	8.3ms, Half Sine pulse	120	A

### Electrical Characteristics:

Characteristics	Symbol	Condition	Typ.	Max.	Units
Forward Voltage Drop(Per Leg)*	V <sub>F1</sub>	@ 2.5A, Pulse, T <sub>J</sub> = 25 °C @ 5A, Pulse, T <sub>J</sub> = 25 °C	0.55 0.69	- 0.75	V
	V <sub>F2</sub>	@ 2.5A, Pulse, T <sub>J</sub> = 125 °C @ 5A, Pulse, T <sub>J</sub> = 125 °C	0.50 0.61	- 0.68	V
Reverse Current(Per Leg)*	I <sub>R1</sub>	@V <sub>R</sub> = rated V <sub>R</sub> T <sub>J</sub> = 25 °C	0.006	0.5	mA
	I <sub>R2</sub>	@V <sub>R</sub> = rated V <sub>R</sub> T <sub>J</sub> = 125 °C	2.0	20	mA
Junction Capacitance(Per Leg)	C <sub>T</sub>	@V <sub>R</sub> = 5V, T <sub>C</sub> = 25 °C f <sub>SIG</sub> = 1MHz	245	-	pF

\* Pulse width < 300 μs, duty cycle < 2%

### Thermal-Mechanical Specifications:

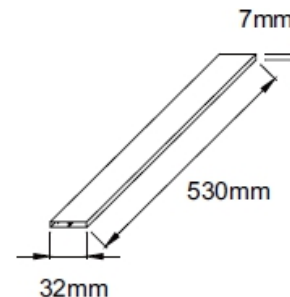
Characteristics	Symbol	ST10100C	STB10100C	STD10100C	STF10100C	Units
Junction Temperature	T <sub>J</sub>	-55 to +150				°C
Storage Temperature	T <sub>stg</sub>	-55 to +150				°C
Typical Thermal Resistance Junction to Case(Per Leg)	R <sub>θJC</sub>	3.0	3.0	2.4	5.5	°C/W

### Tube Specification

Device	Package	Weight	Shipping
ST10100C	TO-220AB	2.0	50pcs / tube
STB10100C	D <sup>2</sup> PAK	1.85	800pcs / reel
STD10100C	DPAK	0.39	2500pcs / reel
STF10100C	ITO-220AB	2.0	50pcs / tube

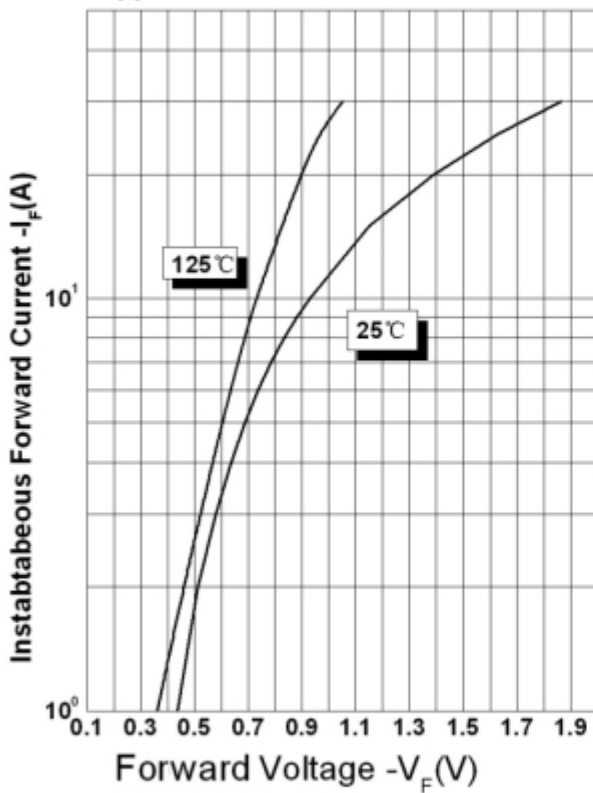
For information on tape and reel specifications, including part orientation and tape sizes, please refer to our tape and reel packaging specification.

### Tube Specification(TO-220AB/ITO-220AB)

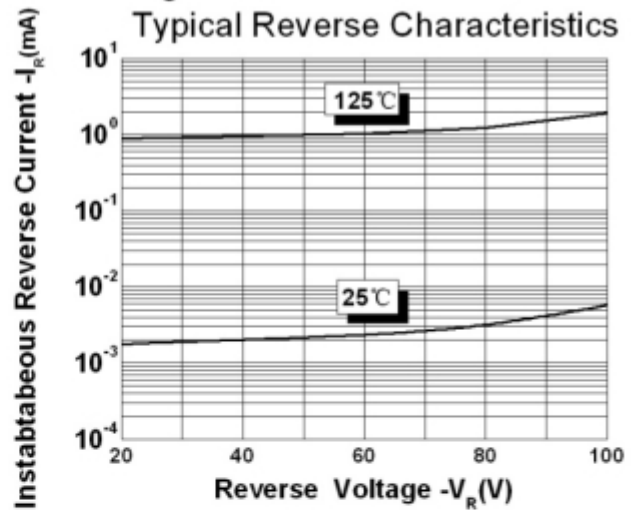


**Ratings and Characteristics Curves**

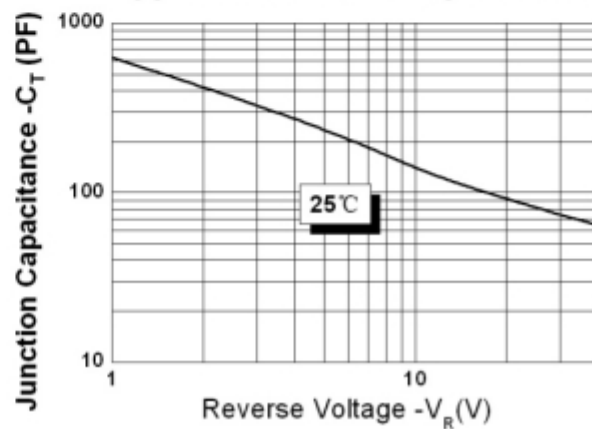
**Figure 1**  
Typical Forward Characteristics



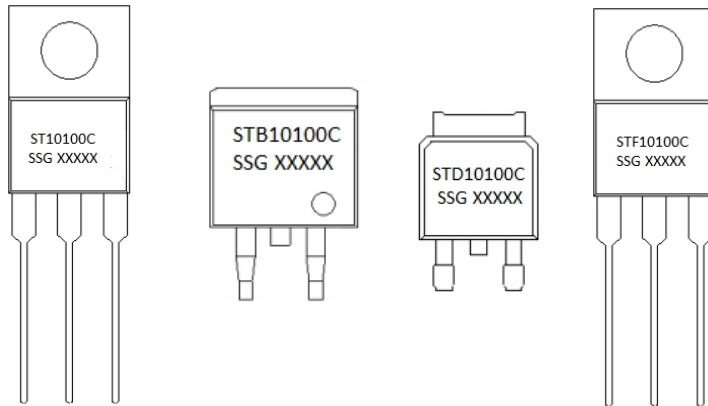
**Figure 2**  
Typical Reverse Characteristics



**Figure 3**  
Typical Junction Capacitance



## Marking Diagram

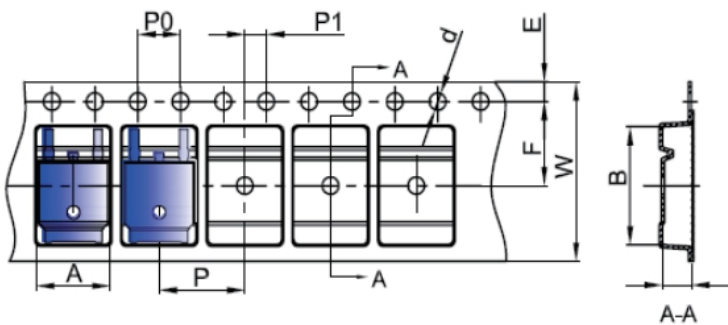


Where XXXXX is YYWWL

ST = Device Type  
B/D/F = Package type  
10 = Forward Current (10A)  
100 = Reverse Voltage (100V)  
C = Configuration  
SSG = SSG  
YY = Year  
WW = Week  
L = Lot Number

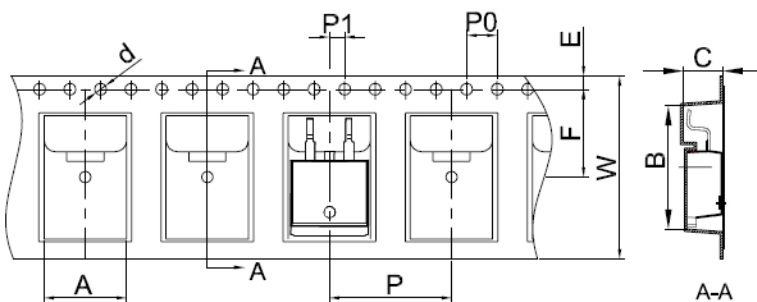
**Cautions:** Molding resin  
Epoxy resin UL:94V-0

## Carrier Tape Specification DPAK



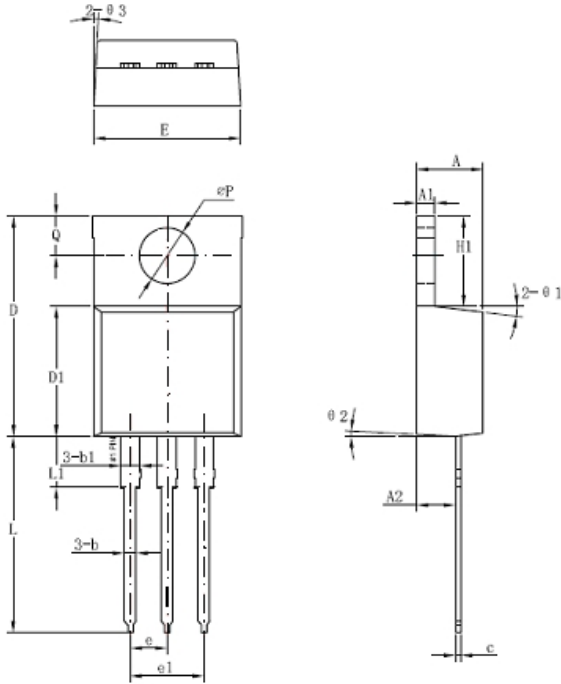
SYMBOL	Millimeters	
	Min.	Max.
A	6.80	7.00
B	10.40	10.60
C	2.60	2.80
d	Φ1.45	Φ1.65
E	1.65	1.85
F	7.40	7.60
P0	3.90	4.10
P	7.90	8.10
P1	1.90	2.10
W	15.90	16.30

## Carrier Tape Specification D2PAK



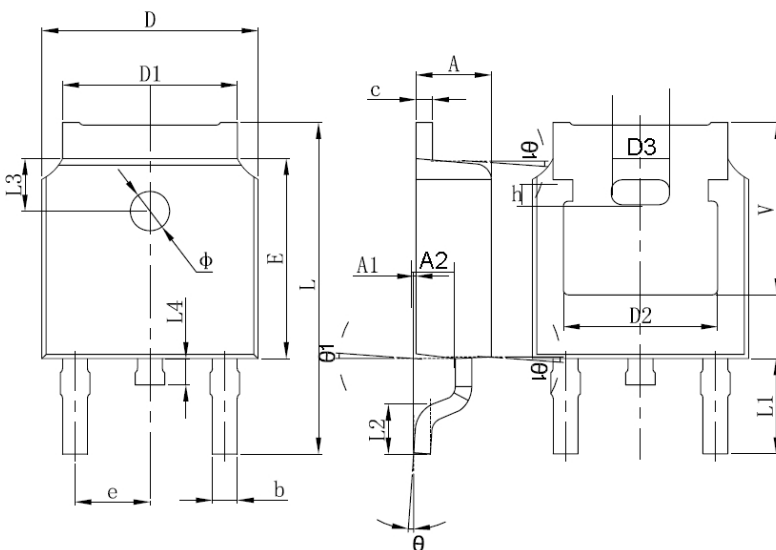
SYMBOL	Millimeters	
	Min.	Max.
A	10.70	10.90
B	16.03	16.23
C	5.11	5.31
d	1.45	1.65
E	1.65	1.85
F	11.40	11.60
P0	3.90	4.10
P	15.90	16.10
P1	1.90	2.10
W	23.90	24.30

**Mechanical Dimensions TO-220AB**



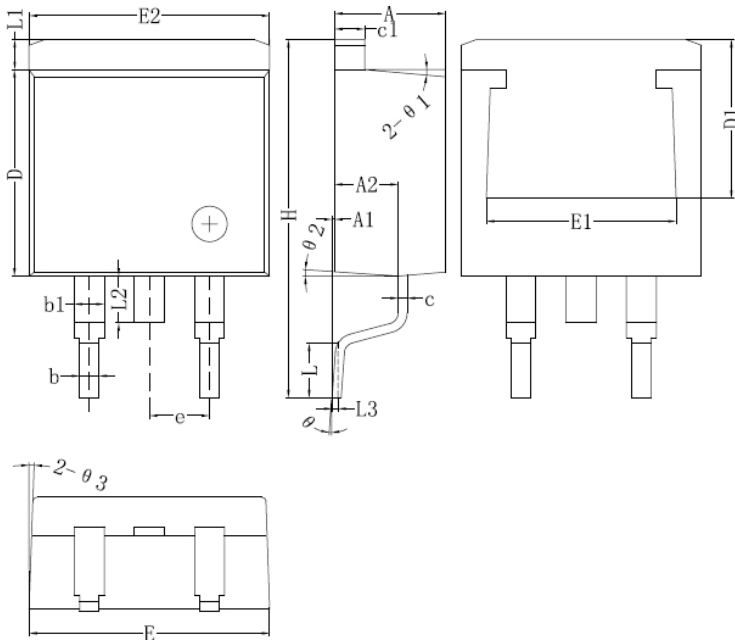
Symbol	Dimensions in millimeters		
	Min	Typical	Max
A	3.56	-	4.83
A1	0.51	-	1.40
A2	2.03	-	2.92
b	0.38	-	1.02
b1	1.14	-	1.78
c	0.31	-	0.61
D	14.22	-	16.51
D1	8.38	-	9.42
E	9.65	-	10.67
e	-	2.54	-
e1	-	5.08	-
H1	5.84	-	6.86
L	12.70	-	14.73
L1	-	-	6.35
ΦP	-	3.56	-
Q	2.54	-	3.43

**Mechanical Dimensions DPAK**



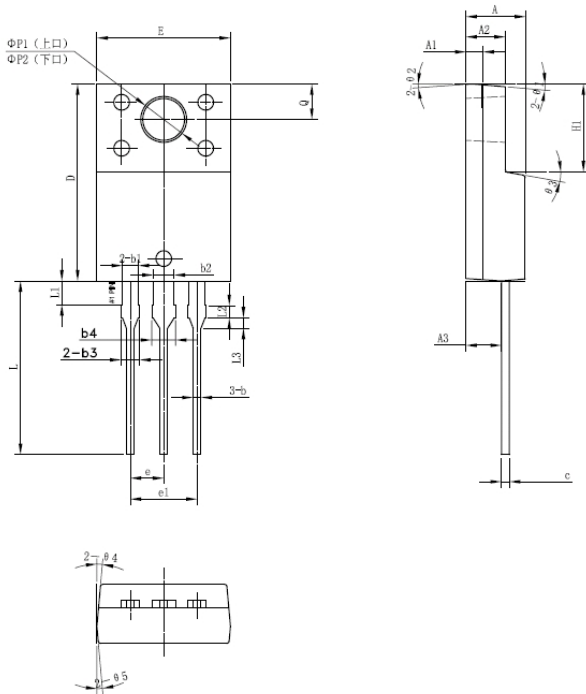
SYMBOL	Dimensions in millimeters		
	Min.	Typ.	Max.
A	2.18	-	2.39
A1	-	-	0.13
b	0.64	-	0.89
c	0.46	-	0.89
D	6.35	-	6.73
D2	4.32	-	-
E	5.97	6.10	6.22
e	2.29BSC		
L	9.40	-	10.41
L2	1.40	1.52	1.78
L4	-	-	1.02
θ	0°	-	10°
V	5.21	-	-

**Mechanical Dimensions D<sup>2</sup>PAK**



Symbol	Dimensions in millimeters	
	Min.	Max.
A	4.06	4.83
A1	0	0.26
b	0.51	0.99
b1	1.14	1.78
c	0.31	0.74
c1	1.14	1.65
D	8.38	8.65
D1	6.86	
E1	6.22	
E2	9.65	10.67
e	2.54BSC	
H	14.60	15.88
L	1.78	2.80
L1	-	1.68
L2	-	1.78
L3	0.255BSC	
Θ	0	8°

**Mechanical Dimensions ITO-220AB**



Symbol	Dimensions in millimeters		
	Min.	Typical	Max.
A	4.30	4.50	4.70
A1	1.10	1.30	1.50
A2	2.80	3.00	3.20
A3	2.50	2.70	2.90
b	0.50	0.60	0.75
b1	1.10	1.20	1.35
b2	1.50	1.60	1.75
b3	1.20	1.30	1.45
b4	1.60	1.70	1.85
c	0.50	0.60	0.75
D	14.80	15.00	15.20
E	9.96	10.16	10.36
e	2.55		
e1	5.10		
H1	6.50	6.70	6.90
L	12.70	13.20	13.70
L1	1.60	1.80	2.00
L2	0.80	1.00	1.20
L3	0.60	0.80	1.00
ΦP1(上口)	3.30	3.50	3.70
ΦP2(下口)	2.99	3.19	3.39
Q	2.50	2.70	2.90
Θ1	5°		
Θ2	4°		
Θ3	10°		
Θ4	5°		
Θ5	5°		



ST10100C  
STB10100C  
STD10100C  
STF10100C

**Technical Data**  
**Data Sheet N1040, Rev. C**



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